

LISTING OF THE CLAIMS:

Please **cancel** claims 36-39 without prejudice.

Please **amend** the claims as follows:

27. (Currently amended) A method of forming a metal pattern, the method comprising:
forming an organometallic layer by coating a photosensitive organometallic complex, wherein the photosensitive organometallic layer consisting of one of an Ag transition compound containing Ag and an ultraviolet sensitive organic ligand or an Al transition compound containing Al and an ultraviolet sensitive organic ligand ;
exposing the organometallic layer to light through a photo mask; and
forming a final metal pattern directly from developing the organometallic layer.
28. (Previously presented) The method of claim 27 wherein the development of the organometallic layer is made by way of an organic solvent.
29. (Previously presented) The method of claim 27 wherein the light-blocking pattern of the photo mask is positioned at the area external to the area to be provided with the metal pattern.
30. (Currently amended) A method of manufacturing a thin film transistor array panel, the method comprising:
forming a gate wire on an insulating substrate, the gate wire including a gate line, a gate electrode and a gate pad;
sequentially depositing a gate insulating layer, an amorphous silicon layer and an ohmic contact layer on the gate wire;
patterning the ohmic contact layer and the amorphous silicon layer by photolithography;
forming a data wire on the ohmic contact layer, the data wire including source and drain electrodes, a data line and a data pad;
forming a protective layer on the data wire;

forming an embossed surface structure of the protective layer, and having a first contact hole exposing the drain electrode, a second contact hole exposing the gate pad and a third contact hole exposing the data pad in the protective layer, simultaneously, using one photoresist pattern having a position dependent thickness, wherein the photoresist pattern has a first portion, a second portion and a third portion and wherein the third portion has a zero thickness and the second portion has a thickness greater than the first portion of the photoresist pattern; and

forming a pixel electrode, a subsidiary gate pad and a subsidiary data pad on the protective layer, the pixel electrode being connected to the drain electrode through the first contact hole, the subsidiary gate pad being connected to the gate pad through the second contact hole, the subsidiary data pad being connected to the data pad through the third contact hole;

wherein at least one of the formations of the gate wire, the data wire and the pixel electrode comprises:

forming an organometallic layer by coating a photosensitive organometallic complex, wherein the photosensitive organometallic layer consisting of one of an Ag transition compound containing Ag and an ultraviolet sensitive organic ligand or an Al transition compound containing Al and an ultraviolet sensitive organic ligand;

placing a photo mask over the organometallic layer such that a predetermined region of the organometallic layer is exposed;

exposing the organometallic layer to light through a photo mask; and

developing the organometallic layer to thereby directly form at least one of the gate wire, the data wire and the pixel electrode.

31. (Currently amended) A method of manufacturing a thin film transistor array panel, the method comprising the steps of:

forming a gate wire on an insulating substrate, the gate wire having gate lines, gate electrodes and gate pads;

sequentially depositing a gate insulating layer, an amorphous silicon layer, an ohmic contact layer and a metallic layer on the gate wire;

patterning the metallic layer, the ohmic contact layer and the amorphous silicon layer by photolithography to form a data wire and channel portions, the data wire having source and drain electrodes, data lines and data pads, the channel portions being placed between the source and the drain electrodes;

forming a protective layer on the data wire;

forming an embossed surface structure of the protective layer and having first to third contact holes in the protective layer, simultaneously, using one photoresist pattern having a position dependent thickness, wherein the photoresist pattern has a first portion, a second portion and a third portion and wherein the third portion has a zero thickness and the second portion has a thickness greater than the first portion of the photoresist pattern; and

forming a pixel electrode, a subsidiary gate pad and a subsidiary data pad on the protective layer, the pixel electrode being connected to the drain electrode through the first contact hole, the subsidiary gate pad being connected to the gate pad through the second contact hole, the subsidiary data pad being connected to the data pad through the third contact hole;

wherein at least one of the steps of forming the gate wire, the data wire and the pixel electrode comprises the sub-steps of:

forming an organometallic layer by coating a photosensitive organometallic complex, wherein the photosensitive organometallic layer consisting of an Ag transition compound containing Ag and an ultraviolet sensitive organic ligand or an Al transition compound containing Al and an ultraviolet sensitive organic ligand;

placing a photo mask over the organometallic layer such that a predetermined region of the organometallic layer is exposed to the outside;

exposing the organometallic layer to light by the photo mask; and

developing the organometallic layer to thereby directly form at least one of the gate wire, the data wire and the pixel electrode.

32. (Previously presented) The method of claim 30 or 31 wherein the development of the organometallic layer is made by way of an organic solvent.

33. (Previously presented) The method of claim 30 or 31 wherein the light-blocking

pattern of the photo mask is positioned at the area external to the area to be made of the signal wire or the pixel electrode.

34. (Previously presented) The method of claim 30 or 31 wherein the metal is Ag.

35. The method of claim 30 or 31 wherein the protective layer has a surface with prominent and depressed portions.

36-39 (Canceled)

40. (New) The method of claim 30, wherein the protective layer is formed with an embossed surface, and wherein at least one of the pixel electrode, the subsidiary gate pad and the subsidiary data pad is formed directly on the embossed surface of the protective layer.

41. (New) The method of claim 31, wherein the protective layer is formed with an embossed surface, and wherein at least one of the pixel electrode, the subsidiary gate pad and the subsidiary data pad is formed directly on the embossed surface of the protective layer.

42. (New) The method of claim 27, wherein the transition compound includes Ag.

43. (New) The method of claim 27, wherein the transition compound includes Al.

44. (New) The method of claim 30, wherein the transition compound includes Al.

45. (New) The method of claim 31, wherein the transition compound includes Al.